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Mfg. semiconductor devices by semiconductor-on insulator technology - by irradiating layer through windows in anti reflection film to form recrystallised areas

C86-046004 E(DE FR GB)

L(4-C14,4-E1A)

The device is mfd. by:
(i) forming an amorphous or poly semiconductor layer on an amorphous insulating layer;
(ii) adding an anti-reflecting film;
(iii) forming windows in the film;
(iv) irradiating to recrystallise the layer in the windows; and
(v) forming devices or active regions in the recrystallised areas.

Semiconductor is specifically Si; anti-reflecting layer is Si_3N_4 or SiO_2/Si_3N_4.

USE

In an IGFET device in which the channel region is formed in the recrystallised area. (claimed).

ADVANTAGE

Device areas can be formed with random layout and with high device yield.

SPECIFICALLY

Insulated gate electrode is formed in a recrystallised area, with source and drain regions formed abutting the area. The electrode insulating layer is SiO_2, pref. formed using LPCVD or thermal oxidn.

Irradiation beam is a laser, esp. an Ar ion laser, scanned over the anti-reflecting layer so that the regions in the windows are consecutively recrystallised.(29pp1550KJP DwgNo0/5).

(E)ISR: No Search Report.

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recrystallize w/cap layer

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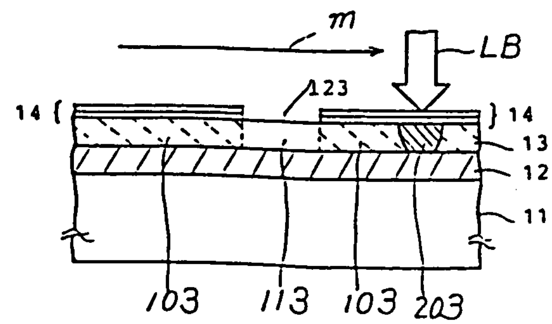
(54) **A manufacturing method of an integrated circuit based on the semiconductor-on-insulator technology and a device so manufactured.**

(57) Random layout of devices or active regions of the devices is allowed for a semiconductor integrated circuit based on an SOI technology using an anti-reflecting film (14). Openings (123) are provided for the anti-reflecting film (14) formed on a polycrystalline silicon layer (13), corresponding to the device regions wherein devices or active regions of the devices are to be formed. An overlapped scan of a laser (LB) beam having diameter larger than the dimension of the openings (123) is applied on the silicon layer (13) through the openings and circumferential anti-reflecting film (14). Concaved temperature profile is achieved along every directions (m) across the openings due to the enhanced beam (LB) absorption by the circumferential anti-reflecting film (14), hence recrystallization nucleation of the silicon layer initiates at the center of each opening during the laser beam scan. Thus, self-aligned single crystal regions (113) are fabricated in the polycrystalline silicon layer (13) at the respective predetermined device regions. The channel region of an IG-FET is exclusively formed in the single crystal region (113) and the source or drain regions are formed in adjacent polysilicon regions.

FIG. 4(c)



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TITLE OF THE INVENTION

A Fabrication Method of a Semiconductor Integrated Circuit and a Device Fabricated by Using the Same

BACKGROUND OF THE INVENTION

The present invention relates to a semiconductor device based on so-called SOI (semiconductor on insulator) technology, particularly to a method for fabricating the semiconductor device by using an anti-reflecting film for laser beam irradiation.

SOI technology has been receiving increasing interests because of its attractive capabilities of providing integrated circuits (ICs) with increased breakdown voltages between isolated circuit components such as transistors and so forth, and also with improved operating speeds due to reduced parasitic capacitances between the circuit components and a substrate the circuit components formed thereon. The outstanding feature of SOI technology is the capability of providing three-dimensional ICs considered as the most promising means of breakthrough for the limitation to the integration density in conventional ICs.

In the early stage of SOI technology, efforts were directed to obtaining a recrystallized region as large as possible in a polycrystalline semiconductor layer such as a polysilicon layer. This resulted in the difficulty of forming a grain boundary free region at desired position in the semiconductor layer. If a grain boundary locates in

the active region of a transistor, for example, formed in the recrystallized region, characteristics of the transistor cannot be comparable to ordinary transistors fabricated on single crystal silicon substrates. Such grain boundary becomes the causes of increased leakage currents and nonuniformity of threshold voltages of the transistors.

Recent development in the SOI technology rather seems to be concentrated to selective recrystallization of an amorphous or polycrystalline semiconductor layer. That is, only predetermined regions of a semiconductor layer, in each of which an active component such as transistor is to be formed, are recrystallized into single crystal islands. Though originally proposed for increasing efficiency of the light beam irradiation for recrystallizing a semiconductor layer, anti-reflecting film coating has been reported to be advantageous for such selective recrystallization if it is modified into a stripe structure. (Colinge et al; Applied Physics Letters, vol.41, p.346, 1982). In this method, transversely arranged stripes of anti-reflecting film are formed on a amorphous or polycrystalline silicon layer. A laser beam having diameter large enough to cover at least two adjacent stripes is scanned along the center line between the stripes. The laser beam energy is controlled to be at slightly above the lowest level necessary for melting the uncoated region of the silicon layer. Thus, a desired concaved temperature profile in the lateral

direction can be achieved thanks to the greater beam absorption by the stripes of anti-reflecting film. This method will be described in some detail in the following.

FIGs.1(a) and 1(b) are schematic illustrations of an amorphous or polycrystalline silicon layer and stripe-structured anti-reflecting films successively formed on an amorphous insulating layer, wherein FIG.1(a) is a plan view and FIG.1(b) is a cross-section taken along the line B-B in FIG.1(a).

Referring to FIG.1(a) and 1(b), an amorphous or polycrystalline silicon layer 22, which is to be recrystallized into a single crystal, is deposited on an amorphous insulating layer 21. An anti-reflecting film 23 of silicon nitride, Si_3N_4, is formed on the silicon layer 22, and then, delineated into stripe structures 23 as shown in FIGs.1(a) and 1(b). If thickness of the anti-reflecting film stripes 23 is adequately controlled, the reflectivity of the surface of the silicon layer 22 at the region coated with the stripe 23 can approximately be 5% in contrast to that of 60% at the uncoated region. As a result, when a irradiation or laser beam, an argon ion laser beam, for example, having a spot diameter larger than the distance between the stripes 23 is applied, temperature distribution profile as shown in FIG.1(c) is obtained in the lateral direction (i.e. the direction along B-B line in FIG.1(a)). In FIG.1(c), ordinate indicates temperature T and abscissa indicates the position between the stripes 23. As shown in

FIG.1(c), the temperature T is lowest at the center of the stripes 23.

When a laser beam is scanned along the center line between the stripes 23 in the direction as indicated by the arrow in FIG.1(a), recrystallization front edges in the silicon layer is schematically indicated by a curve 25 which moves upward according to the scanning of the laser beam. In FIG.1(a), two curves 25 correspond to respective recrystallization fronts at two different moments. Each of the curves 25 indicates a solid-liquid interface and melting point of the silicon layer 22 distributes along the curve 25. Because the curve 25 (solid-liquid interface line) has curvature bending behind the front edge, the growth of a crystal grain nucleated from a virtual seed on the center line is dominant, and finally, spreads over the region between the stripes 23. As a result, grain boundaries between the above mentioned dominant grain and other subdominant grains are going to be swept from the region between the stripes 23 and accumulate under the stripes 23. Similar concaved temperature profile is obtained by using a doughnut-shaped laser beam and successful recrystallization is achieved in a polysilicon layer on an amorphous layer. (Kawamura et al; Applied Physics Letters, vol.40, p.394, 1982)

Thus, with the use of anti-reflecting film stripes, it is reported that a single crystallized region of 20x100 square microns can be formed in a silicon layer on an

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amorphous insulating layer. The stripe-structured anti-reflecting film permits laser beam to be efficient and simple of its shape as a round beam. However, the stripe-structured anti-reflecting film methodology inevitably decreases the freedom in the device pattern layout on a semiconductor layer.

Referring to FIGs.1(a) and 1(b), if devices such as transistors or at least active regions of the devices are respectively located in regions 26a and 26b of the semiconductor layer 22, one of the devices or active regions of the devices can be formed in a single-crystallized region 26a, but another formed in a region 26b can not be free of a grain boundary because of the reason as described before. Since grain boundaries provide the device with the aforesaid undesirable influences, the device pattern layout can not but be restricted within the region between the anti-reflecting film stripes 23. This means that random layout of the devices or active regions of the devices is substantially inhibited and the devices or the active regions must be positioned in a relatively orderly arrangement instead. As a result, SOI technology using anti-reflecting film stripes is suitable to integrated circuits (ICs) such as those based on gate array methodology but is rather not suitable to ICs requiring random arrangement of devices as in logic ICs. Thus, the anti-reflecting film stripe

methodology also restricts efficient use of semiconductor area in ICs based on SOI.

SUMMARY OF THE INVENTION

It is an object of the present invention to provide a semiconductor integrated circuit based on an SOI technology using an anti-reflecting film, wherein the layout of devices on a semiconductor layer can be substantially random.

It is another object of the present invention to provide a semiconductor integrated circuit based on an SOI technology using an anti-reflecting film, wherein effective use of semiconductor area can be achieved.

It is further another object of the present invention to provide an insulated-gate transistor based on an SOI technology with improved fabrication yield.

The above objects can be attained by fabricating a semiconductor integrated circuit based on an SOI technology using an anti-reflecting layer but not in the form of stripes. The fabrication method comprising steps of: (a) forming an amorphous or polycrystalline semiconductor layer on an amorphous insulating layer; (b) forming an anti-reflecting film to a light beam on the semiconductor layer; (c) selectively forming openings at respective predetermined portions of the anti-reflecting film; (d) irradiating the light beam to an area of surface of the anti-reflecting film, the area including at least one of

the openings, on conditions that the semiconductor layer is recrystallized to be free of grain boundaries at the opening; and (e) forming a semiconductor device or active region of the device in the recrystallized semiconductor layer at the opening. In accordance with the method, the channel region of an insulated-gate field effect transistor (IG-FET) or metal oxide semiconductor (MOS) transistor is exclusively formed in a recrystallized semiconductor layer at the opening.

BRIEF DESCRIPTION OF DRAWINGS

The above and other objects and advantages of the present invention will become apparent from the following description of embodiments with reference to accompanying drawings forming a part thereof, wherein:

FIGs.1(a) and 1(b) are schematic illustrations of an amorphous or polycrystalline silicon layer formed on an amorphous insulating layer and stripes of anti-reflecting layer formed on the silicon layer, wherein FIG.1(a) is a plan view and FIG.1(b) is a cross-section taken along the line B-B in FIG.1(a);

FIG.1(c) is a temperature distribution profile obtained in the direction along B-B line in FIG.1(a);

FIGs.2(a) and 2(b) are a plan view and enlarged cross-section taken along line B-B in FIG.2(a) in accordance with an embodiment of the present invention.

FIG.3(a) is a plan view schematically illustrating the growth of single recrystallized region at an opening according to the present invention;

FIGs.3(b) and 3(c) are respective temperature distribution profiles on the lines E-E and F-F in FIG.3(a);

FIGs.4(a) to 4(g) are cross-sections at the respective fabrication steps of a semiconductor device based on an SOI technology; and

FIGs.5(a) to 5(d) show yet another embodiment of the present invention.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

An embodiment of the present invention is shown in a plan view of FIG.2(a) and an enlarged cross-section of FIG.2(b) taken along line B-B in FIG.2(b). Referring first to FIG.2(b), as a substrate, an insulating layer of SiO_2 layer 4 of thickness of about 1 micron is formed on a silicon wafer 3 by using a thermal oxidation process, for example. Respective one of silicon nitride layer 5 and polysilicon layer 6 having thicknesses of 1000 Å and 4000 Å, respectively, are successively formed on the SiO_2 layer 4 by using low pressure chemical vapor deposition (LPCVD) methods, for example. The polysilicon layer 6 is the layer to be subject to a recrystallization process later, and the silicon nitride layer 5 is for improving adhesion of the polysilicon layer 6 to the SiO_2 layer 4 after the recrystallization. A SiO_2 layer 7 of about 300 Å is formed

by thermally oxidizing the surface of the polysilicon layer 6 and then a silicon nitride layer 8 of about 300 Å is deposited thereon by using an LPCVD method, for example. The SiO_2 layer 7 and silicon nitride layer 8 constitute anti-reflecting film 2 in FIG.2(a). The thickness of the anti-reflecting film 2 is determined according to the wave length of laser beam for the recrystallization and the refractive index of the layer materials to the wave length. The anti-reflecting film may comprises a single layer of either of SiO_2 or silicon nitride, however, the double-layered structure of the anti-reflecting film allows to take advantages as described in later.

Referring back to FIG.2(a), the anti-reflecting layer 2 is provided with substantially rectangular-shaped openings (windows) 1a, 1b, 1c and so forth, instead of being formed into the stripe structure in the prior art as shown in FIGs.1(a) and 1(b). Each of the openings is positioned so as to correspond to a device region (the region in which a device such as transistor or the active region such as channel region of the transistor is formed). The dimension of the opening is 10 to 20 microns, for example.

A light beam from a cw (continuous wave) Ar ion laser, for example, having output power of 8 to 14 watts is scanned over the anti-reflecting film 2 and the polysilicon layer at the openings 1a, 1b, 1c and so forth at a speed of 5 cm/sec. The scan of the laser beam is carried out by

translating the wafer 3 relative to a fixed beam or it may be done vice versa, wherein scanning pitch is controlled to be smaller than the diameter of the beam D so that the traces of the scanned beam overlap each other. A preferable overlap ratio is approximately 70 per cent of the beam diameter. The beam diameter D is 80 to 100 microns in terms of the width of irradiated region on the substrate. The dimension of an opening is 10 to 20 microns as mentioned before. Hence, since the beam is relatively larger than the openings (4 to 10 times) and the scanning speed is relatively high compared with the dimension of openings, the polysilicon layer at each opening can be assumed to be heated with a pulse of a fixed beam. In the above, the beam for the recrystallization should not be limited to a laser beam but other energy beam such as a focused emission of a mercury lamp may be employed if it can provide a sufficient energy density.

FIG.3(a) is a plan view schematically illustrating the growth of single recrystallized region in an opening, for example, the opening 1a in FIg.2(a). FIGs.3(b) and 3(c) are temperature distribution profiles along the lines E-E and F-F in FIG.3(a), respectively, wherein T indicates temperature and coordinates on the respective axes perpendicular to the temperature axes indicate the position on lines E-E and F-F. The same as in the prior art using stripe-structured anti-reflecting film as described with reference to FIGs.1(a) to 1(c), the temperature T is lowest

at the center of the opening 1a in both E-E and F-F directions and increases toward the periphery of the opening 1a because of the greater absorption of the laser beam irradiation by the anti-reflecting film 2. As a result, recrystallization of the polysilicon layer initiates from the nucleus 9 at the center of the opening immediately after the cease of the pulsed laser beam irradiation. A substantially isotropic recrystallization occurs to spread as shown by circles 10 in FIG.1(a), and finally, fills in the opening 1a. Thus, a grain-boundary-free single crystal polysilicon layer is formed in the opening 1a, and similarly in other openings.

Another embodiment of the present invention will be described in the following with reference to FIGs.4(a) to 4(g) illustrating cross-sections at the respective fabrication steps of a semiconductor device based on SOI technology.

Referring to FIG.4(a), a SiO_2 insulating layer 12 of thickness of about 1 micron is formed on a silicon substrate 11 by using a thermal oxidation process, and then, an amorphous or polycrystalline silicon layer 13 of thickness of about 4000 Å is deposited on the insulating layer 12 by using a CVD (chemical vapor deposition) method. In the following description of this embodiment, a polysilicon layer stands for the silicon layer 13. The polysilicon layer 13 is then doped with a predetermined concentration of boron, B, as a p-type impurity by an ion

implantation technique. Thus, the polysilicon layer 13 is provided with p-type conductivity.

A SiO_2 thin film 121 of thickness of about 300 Å is formed on the polysilicon layer 13 by using a thermal oxidation process, and then a silicon nitride (Si_3N_4) film 122 of thickness of about 300 Å is deposited on the SiO_2 film 121 by a CVD method. The SiO_2 film 121 and Si_3N_4 film 122 are selectively removed as shown in FIG.4(b) by using a conventional photolithographic technique so that openings throughout the films are formed at predetermined regions Ach. Each of the regions is referred to as device region in which an insulated gate field effect transistor (IG-FET) or at least the channel of the transistor is to be formed. In FIG.4(b), only one opening 123 is illustrated.

The SiO_2 film 121 and Si_3N_4 film 122 constitutes an anti-reflecting film to the laser beam irradiation. The anti-reflecting film may comprise either one of SiO_2 or Si_3N_4 film as mentioned before, however, the double-layered anti-reflecting film as shown in FIG.4(b) permit to take advantage of large etching rate difference between SiO_2 and Si_3N_4 or silicon to etchants such as carbon tetra-fluoride (CF_4) gas and a hydrochloric acid (HF) solution. For instance, during a dry etching process for forming the opening 123, the SiO_2 film 121 having a relatively low etching rate compared with those of the Si_3N_4 film 122 and polysilicon layer 13 plays a role of a stopping layer against the etching by an etchant gas such as CF_4 but it

can easily be removed by HF solution without affecting the polysilicon layer 13. Thus, the process for forming precision openings 123 in the anti-reflecting film on the polysilicon layer 123 can be facilitated.

During the substrate 11 is heated at about 450°C in atmospheric air, scan of a laser beam LB, Ar ion laser, for example, in the direction of an arrow m is applied to the polysilicon layer 13 through the anti-reflecting film 14 as shown in FIG.4(c). Hence, every portions of the polysilicon layer 13 are brought into a molten state once according to the scan of the laser beam, and its corresponding region to the opening 123 is recrystallized into a single crystal 113. In FIG.4(c), references 103 and 203 designate a domain recrystallized into a polycrystalline state and that in molten state, respectively.

Intensity and scanning speed of the laser beam LB are controlled to be enough for melting the polysilicon layer 13 under the anti-reflecting film 14 which decreases the reflectivity of the surface of the polysilicon layer 13 to about 5 per cent but insufficient for melting a polysilicon layer alone having surface reflectivity of about 60 per cent alone. (i.e. the laser beam is too week to raise the polysilicon layer 13 at the opening 123 up to the melting point if no anti-reflecting layer 14 is formed around the opening 123.) Exemplary conditions complying with such requirement are as follows:

Laser output: 10 Watts

Laser beam diameter: 50 microns

Scanning speed: 5 cm/sec

In the above, the laser beam diameter is defined in terms of the width of melted region of a polycrystalline layer coated with an anti-reflecting film when a laser beam is scanned thereon.

With the scan of a laser beam under the above conditions, recrystallization of the polysilicon layer 13 initiates at the center of the opening 123 and spreads therein as explained with reference to FIG.3 (a). Thus, the polysilicon layer 13 at the opening 123 becomes single crystal, however, desirable recrystallization into a single crystal layer does not occur in the circumferential polysilicon layer 13 under the anti-reflecting film 14 as mentioned before.

In accordance with the object of the present invention, a number of openings in an anti-reflecting film can be positioned randomly, corresponding to the regions, each for forming a device or active region of the device therein. As a result, it is probable that when a laser beam is scanned with aforesaid overlapping manner, the edge of the laser beam occasionally crosses over an opening at which the polysilicon layer has already been single-crystallized. However, the single-crystallized layer in the region would not be melted again by the laser beam scan, because heat necessary for the

single-crystallized region to reach again its melting point is not supplied from the un-irradiated side region of the opening.

After the polysilicon layer 13 at each opening 123 is recrystallized to be grain boundary free (whereas each corresponding circumferential region is recrystallized as a polycrystal layer), the Si_3N_4 film 122 and SiO_2 film 121 constituting the anti-reflecting film 14 are removed by using a hot phosphoric acid solution and a hydrofluoric acid solution, respectively. Then, the polysilicon layer 13 is formed into islands so that each island includes one of the single-crystallized region 113 and corresponding polycrystalline circumferential region 103, as shown in FIG.4(d).

The surface of the island is thermally oxidized, hence a gate oxide layer 15 having a predetermined thickness is formed as shown in FIG.4(e). Subsequently, a polysilicon layer of thickness of about 4000 Å is formed on the island by a conventional CVD process and selectively etched by using an ordinary photolithographic technique so that a gate electrode 16 is left on the single-crystallized region 113.

Following the above, high concentration of an impurity such as arsenic (As) is ion-implanted into the silicon layer 103 with the use of polysilicon gate electrode 16 as a mask, hence n^+-type source or drain regions 17 and 18 are formed after an annealing at temperature 1050°C, as shown

in FIG.4(f). Thus, basic structure of an insulated-gate field effect transistor (IG-FET) or MOS transistor is completed based on SOI technology.

An insulating coating layer 19 is formed on each of the transistor structure. The insulating coating layer 19 having thickness of about 8000 Å is, then, provided with contact holes 100 through which connections to the source or drain regions 17 and 18 are provided by the respective wiring layers 110 and 120 of aluminum, for example, as shown in FIG.(g). If a PSG (phospho-silicate glass) layer is used for the insulating coating layer 19, a heat process (conventionally referred to as a reflow process) at 1050°C, for example, is needed for blunting the sharp edge of the contact holes 100.

As described above, a heat process at a temperature as high as 1050°C is necessary for the annealing of the ion-implanted source or drain regions 17 and 18 or the reflow process for the contact holes 100 in a PSG layer. The heat process at such high temperature tends to cause diffusion of doped impurities from the source or drain regions 17 and 18 to the single crystal region 113. If a grain boundary should exist in the single crystal region 113, the impurity diffusion along the grain boundary would be accelerated, and thus, the problems in the prior art, such as increased leak currents, non-uniform threshold voltages, source-drain breakdown failures, etc. in the

devices formed in the recrystallized semiconductor layer, would occur.

Again, in the prior art SOI technology using anti-reflecting film, it is substantially impossible to recrystallize a semiconductor layer selectively only at the device regions. As a result, the regions to be grain boundary free are formed inevitably large in order to provide some degree of freedom in the arrangement of the devices. This results in difficulty in the fabrication and poor yield of semiconductor integrated circuits based on the SOI technology. On the other hand, according to the present invention, it is possible to recrystallize a semiconductor layer at arbitrary regions corresponding to the device regions, as explained in the above embodiments. As a result, small semiconductor regions, each of which afford to accommodate at least the active region of a device, for example, a channel region of an IG-FET, can selectively be grain boundary free, corresponding to the device layout. Thus, according to the present invention, the IG-FETs, for example, in a semiconductor integrated circuit based on an SOI technology can be free from the prior art problems relating to the grain boundaries, and therefore, superior characteristics and greater fabrication yield of the integrated circuit can also be provided. It is obvious that entire region of a device including the source or drain regions of an IG-FET, for example, can be fabricated in a grain-boundary-free region formed according

to the present invention, since the grain-boundary-free region can be large as 10x20 square microns.

FIGs.5(a) to 5(d) show further another embodiment of the present invention. A polycrystalline semiconductor layer 41, polysilicon layer, for example, having thickness of about 4000 Å is formed on an insulating layer 40 having thickness of about 1 micron, and an anti-reflecting film 42 having an opening 421 is formed on the polysilicon layer 41, as shown in FIG.5(a). The anti-reflecting film 42 may has a double-layered structure comprising a Si_3N_4 layer 422 and an underlying SiO_2 layer 423, each having a thickness of about 300 Å. The polysilicon layer 41 at the opening 421 is recrystallized to be grain boundary free by a laser beam irradiation, as described in the previous embodiments. The surface of the polysilicon layer 41 at the opening 421 is thermally oxidized to form a SiO_2 layer 411 of thickness of about 1000 Å. The anti-reflecting film 42 protects the polysilicon layer 41 around the opening 421 from the thermal oxidation.

The Si_3N_4 layer 422 of the anti-reflecting film 42 is removed by using a selective etchant such hot phosphoric acid solution. The SiO_2 layer 411 and the exposed SiO_2 layer 423 as shown in FIG.5(b) are subjected to a dry etching process using an etchant such as CF_4 plasma. The time necessary for etching off the 300 Å SiO_2 layer 423 is about 40 seconds and that for the 1000 Å SiO_2 layer 411 is about 120 seconds. Hence, the surface of the polysilicon

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layer 41 around the opening 421 is first exposed to the CF_4 plasma, and subsequently etched off completely before the remaining about 700 Å SiO_2 layer 411 is etched off, as shown in FIG.5(c), because etch rate of silicon by CF_4 plasma is about 100 times larger than that of SiO_2. The dry etching is continued until the SiO_2 layer 411 is just removed, and finally, a single crystal island 412 of silicon is left on the insulating layer 40, as shown in FIG.5(d). Thus, self-aligned single crystal silicon islands can be obtained in accordance with the SOI technology of the present invention.

While the described embodiments represent the preferred form of the present invention, it is to be understood that modifications will occur to those skilled in the art without departing from the spirit of the invention. The scope of the present invention is therefore to be determined by the appended claims.

CLAIMS

1. A fabrication method of a semiconductor device, comprising the steps of:

forming an amorphous or polycrystalline semiconductor layer on an amorphous insulating layer;

forming an anti-reflecting film to a light beam on said semiconductor layer;

selectively forming openings at respective predetermined portions of said anti-reflecting film;

irradiating said light beam to an area of surface of said anti-reflecting film, said area including at least one of said openings, on conditions that said semiconductor layer is recrystallized to be free of grain boundaries at said opening; and

forming a semiconductor device or active region of said device in said recrystallized semiconductor layer at said opening.

2. A fabrication method of a semiconductor device as set forth in claim 1, wherein said semiconductor is silicon.

3. A fabrication method of a semiconductor device as set forth in claim 1, further comprising a step of forming an insulated gate electrode on said recrystallized region of said semiconductor layer, said insulated gate electrode comprising a gate electrode and an insulating layer formed

between said gate electrode and said recrystallized region of said semiconductor layer.

4. A fabrication method of a semiconductor device as set forth in claim 3, further comprising a step of forming respective regions for source and drain in said semiconductor layer, said source and drain regions facing each other across said recrystallized region of said semiconductor layer and abutting said recrystallized region.

5. A fabrication method of a semiconductor device as set forth in claim 3, wherein said semiconductor is silicon.

6. A fabrication method of a semiconductor device as set forth in claim 5, wherein said insulating layer is a silicon dioxide layer.

7. A fabrication method of a semiconductor device as set forth in claim 6, wherein said silicon dioxide layer is formed by using LPCVD (low pressure chemical vapor deposition).

8. A fabrication method of a semiconductor device as set forth in claim 6, wherein said insulating silicon dioxide layer is formed by thermally oxidizing the surface of said recrystallized region of said semiconductor layer.

9. A fabrication method of a semiconductor device as set forth in claim 1, wherein said anti-reflecting layer comprises a silicon nitride layer.

10. A fabrication method of a semiconductor device as set forth in claim 9, wherein said anti-reflecting layer further comprises underlying silicon dioxide layer.

11. A fabrication method of a semiconductor device as set forth in claim 1, wherein said light beam is a laser beam.

12. A fabrication method of a semiconductor device as set forth in claim 11, wherein said laser beam is an Ar ion laser beam.

13. A fabrication method of a semiconductor device as set forth in claim 1, wherein said light beam is scanned over said anti-reflecting layer so that semiconductor regions at said openings are consecutively recrystallized.

14. An insulated-gate field-effect transistor (IG-FET) fabricated in a semiconductor layer formed on an amorphous insulating layer (24, 4, 12, 40), said semiconductor layer (22, 6, 13, 41) having a recrystallized region in which channel region of said IG-FET is exclusively formed.

FIG. 1 (a)

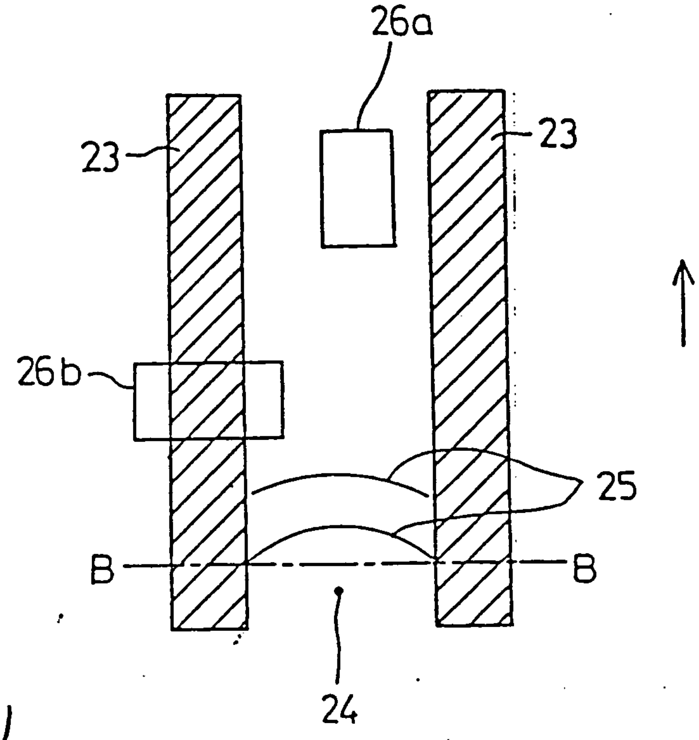

FIG. 1 (b)

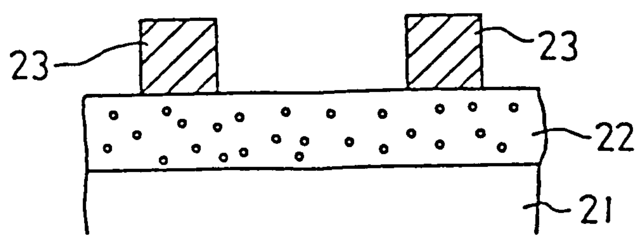

FIG. 1 (c)

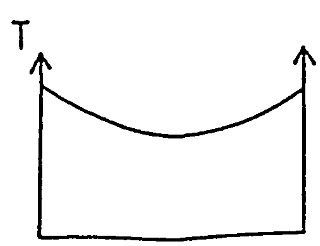

FIG. 2(a)

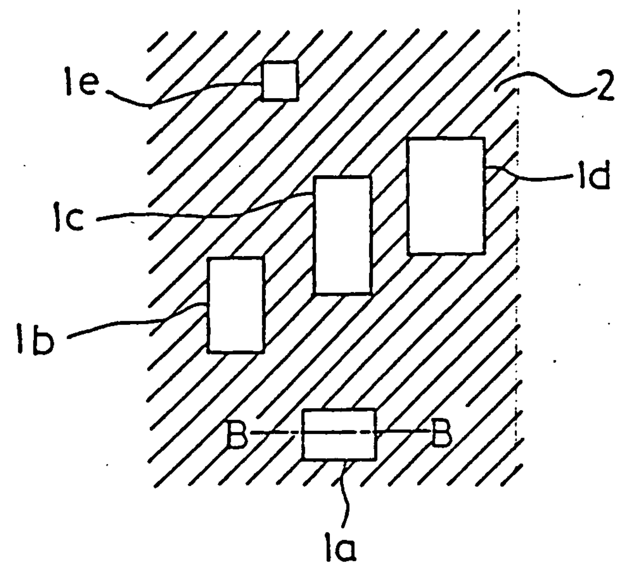

FIG. 2(b)

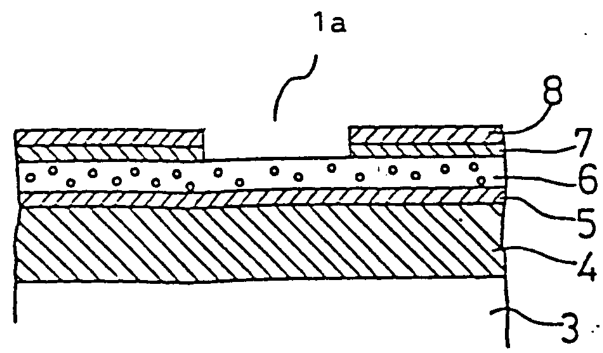

FIG. 3(a)

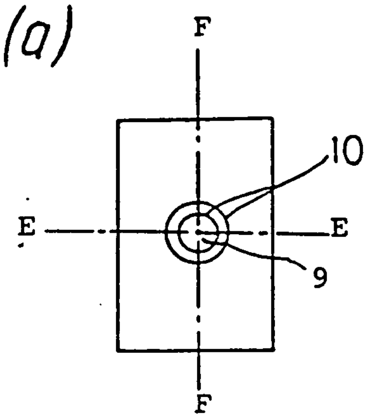

FIG. 3(c)

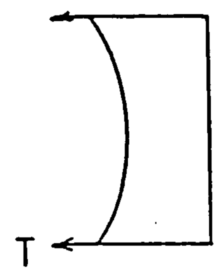

FIG. 3(b)

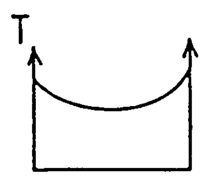

FIG. 4 (a)

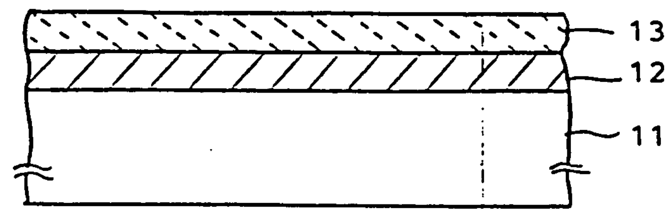

FIG. 4 (b)

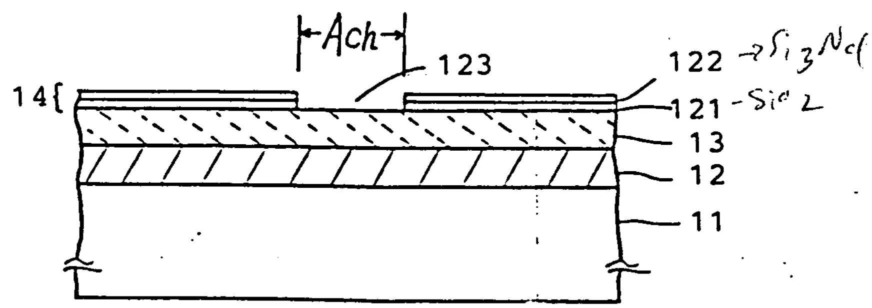

FIG. 4 (c)

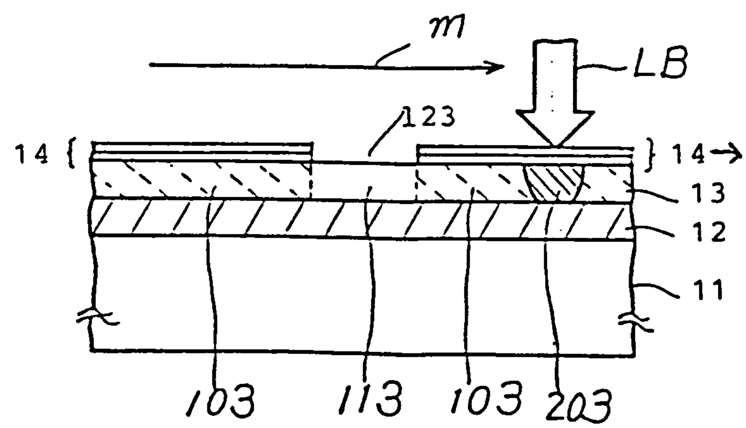

FIG. 4 (d)

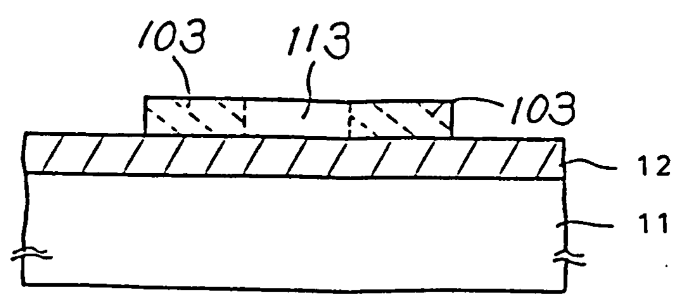

FIG. 4 (e)

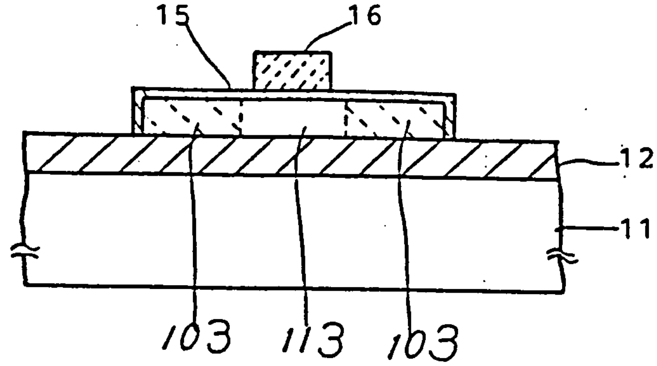

FIG. 4 (f)

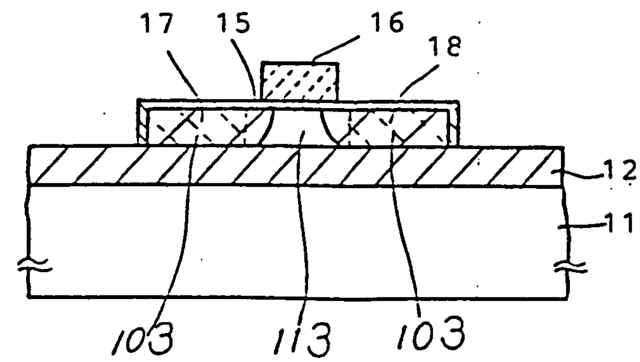

FIG. 4 (g)

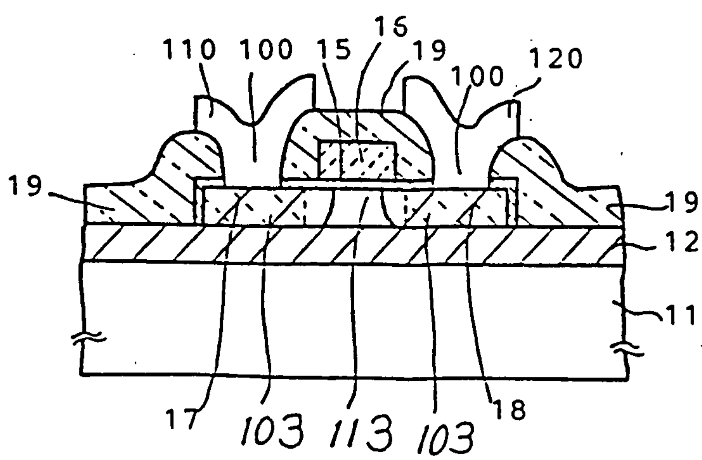

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FIG. 5(a)

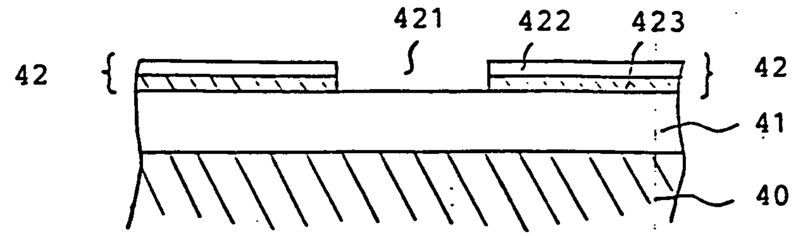

FIG. 5(b)

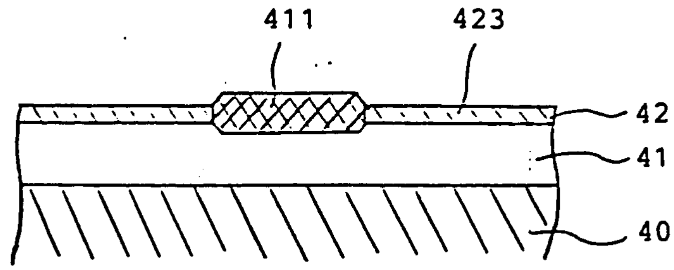

FIG. 5(c)

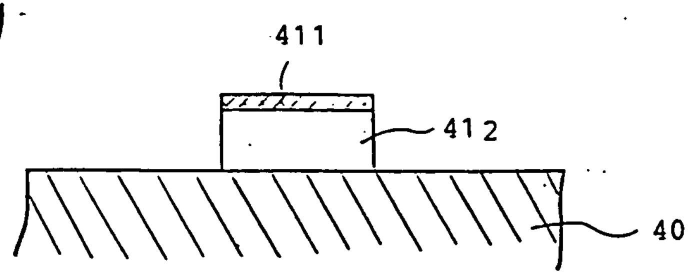

FIG. 5(d)